Docket No.: 2013P148

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

WONJU CHO, ET AL.

Application No.:

Filed:

For: MOSFET DEVICE WITH NANOSCALE

CHANNEL AND METHOD OF MANUFACTURING THE SAME

Art Group:

Examiner:

## INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

-1- 2013P148

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

George W Hoover, Reg. No. 32,992

BL

Date: December 30, 2003

12400 Wilshire Boulevard, 7th Floor Los Angeles, CA 90025 Telephone: (310) 207-3800

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Substitute for form 1449A/PTO

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	2
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Application Numb r				
Filing Date				
First Named Inventor	Wonju Cho			
Art Unit				
Examiner Name				
Attorney Docket Number	2013P148			

U.S. PATENT DOCUMENTS							
ina		Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where		
Examiner Cite No.1		Number - Kind Code² (if known)	or Jeeun Data	Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Examiner Cite No.1	Foreign Patent Document	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear			
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)	MM-DD-YYYY	Applicant of Cited Document	or Relevant Figures Appear			
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Signature	Cons	idered

Based on PTO/SB/08A (08-03) as modified by Blakely, Solokoff, Taylor & Zafman (wir) 08/11/2003.

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<sup>\*</sup>Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

<sup>&</sup>lt;sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

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			JOUKE	Filing Date		
			ICANT	First Named Inventor	Wonju Cho	
				Art Unit		
				Examiner Name		
Sheet	2	of	2	Attorney Docket Number	2013P148	

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
		A. CHATTERJEE, et al. "Sub-100nm Gate Length Metal Gate NMOS Transistors Fabricated by a Replacement Gate Process," Semiconductor Process and Device Center, 1997 IEEE, pps. 821-824	
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